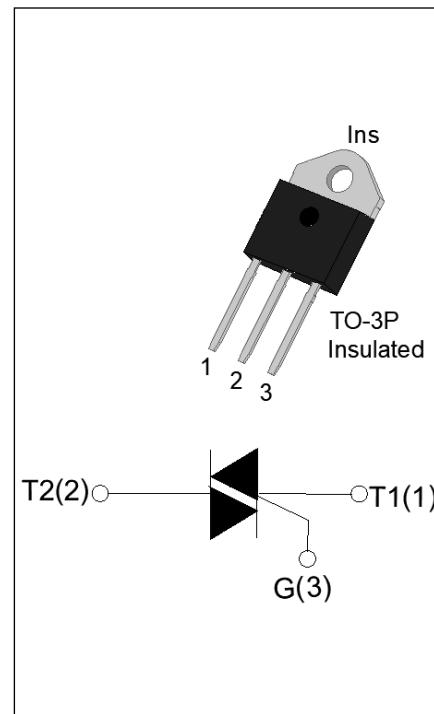


**DESCRIPTION:**

The JST41Z-1200B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an internal ceramic pad, JST41Z-1200B provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
V_{DRM}/V_{RRM}	1200	V
$I_{GT\text{ I/II/III/IV}}$	50/50/50/70	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	V
RMS on-state current ($T_c \leq 78^\circ\text{C}$)	$I_{T(RMS)}$	40	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	420	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		462	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	1000	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	I - II III-IV	100 50	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	8	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	40	W

Peak pulse voltage (T _j =25°C; non-repetitive,off-state;FIG.7)	V _{pp}	1	kV
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ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	I - II -III	MAX.	50	mA
		IV		70	
V _{GT}		ALL	MAX.	1.3	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	I - III-IV	MAX.	80	mA
		II		160	
I _H	I _T =500mA		MAX.	80	mA
dV/dt	V _D =800V Gate Open T _j =125°C		MIN.	800	V/μs
(dV/dt)c	(dI/dt)c=20A/ms, T _j =125°C		MIN.	20	V/μs
t _{on}	I _G =80mA I _A =400mA I _R =40mA T _j =25°C	TYP.	10	μs	
t _{off}			70		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =60A t _p =380μs	T _j =25°C	1.5	V
V _{TO}	Threshold voltage	T _j =125°C	0.72	V
R _D	Dynamic resistance	T _j =125°C	19	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	10	μA
I _{RRM}		T _j =125°C	15	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	0.85	°C/W
R _{th(j-a)}	junction to ambient (AC)	50	°C/W

ORDERING INFORMATION

J	ST	41	Z	-1200	B
JieJie Microelectronics Co., Ltd.					
	Triacs				
		_{T(RMS):40A}			
			Z:TO-3P(Ins)		
				1200:V _{DRM} /V _{RRM} ≥1200V	
					B:I _{G1-3} ≤50mA I _{G4} ≤70mA

MARKING

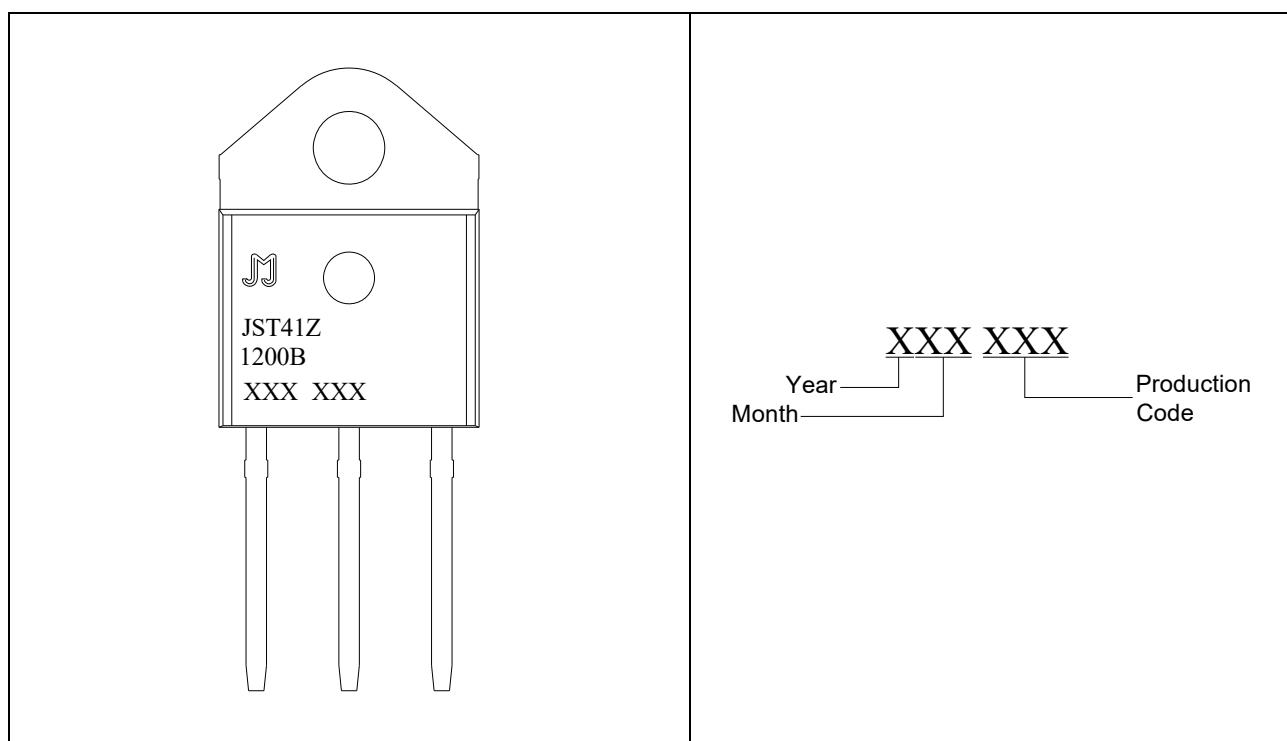


FIG.1 Maximum power dissipation versus RMS on-state current

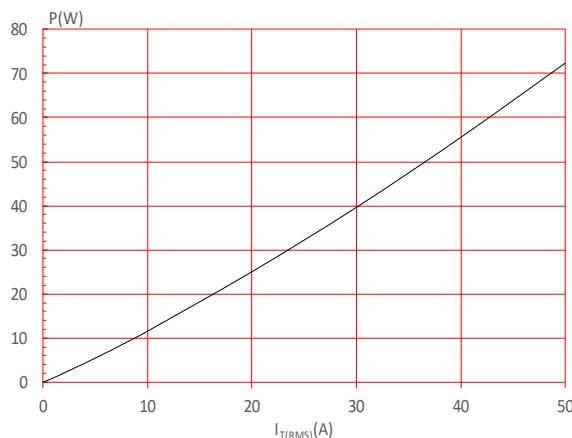


FIG.3: Surge peak on-state current versus number of cycles

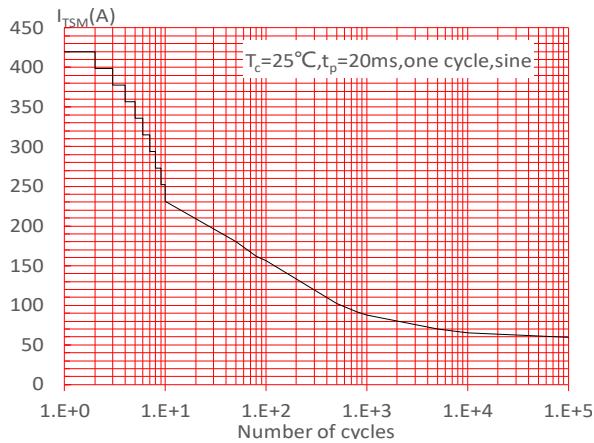


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t
(I - II : $\text{d}I/\text{d}t < 100\text{A}/\mu\text{s}$; III-IV : $\text{d}I/\text{d}t < 50\text{A}/\mu\text{s}$)

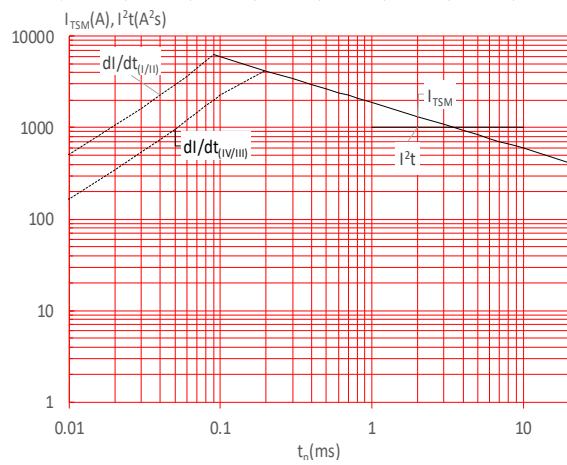


FIG.2: RMS on-state current versus case temperature

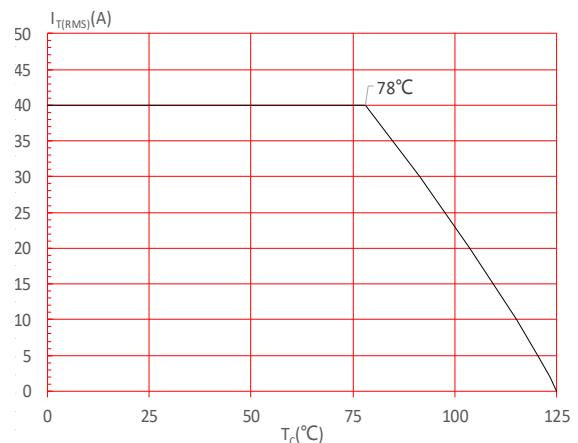


FIG.4: On-state characteristics

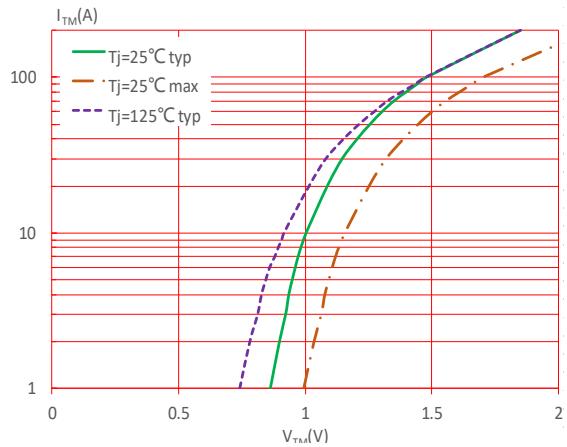


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

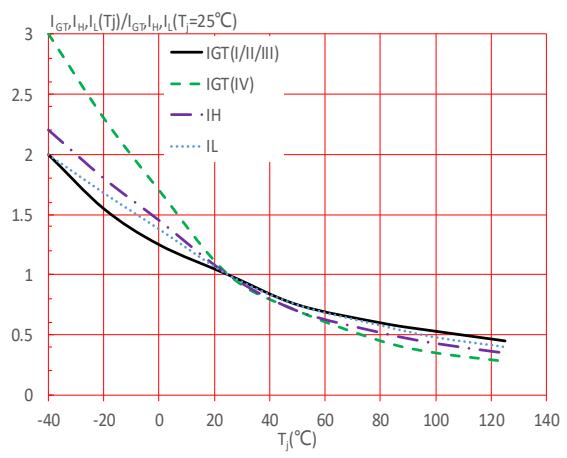
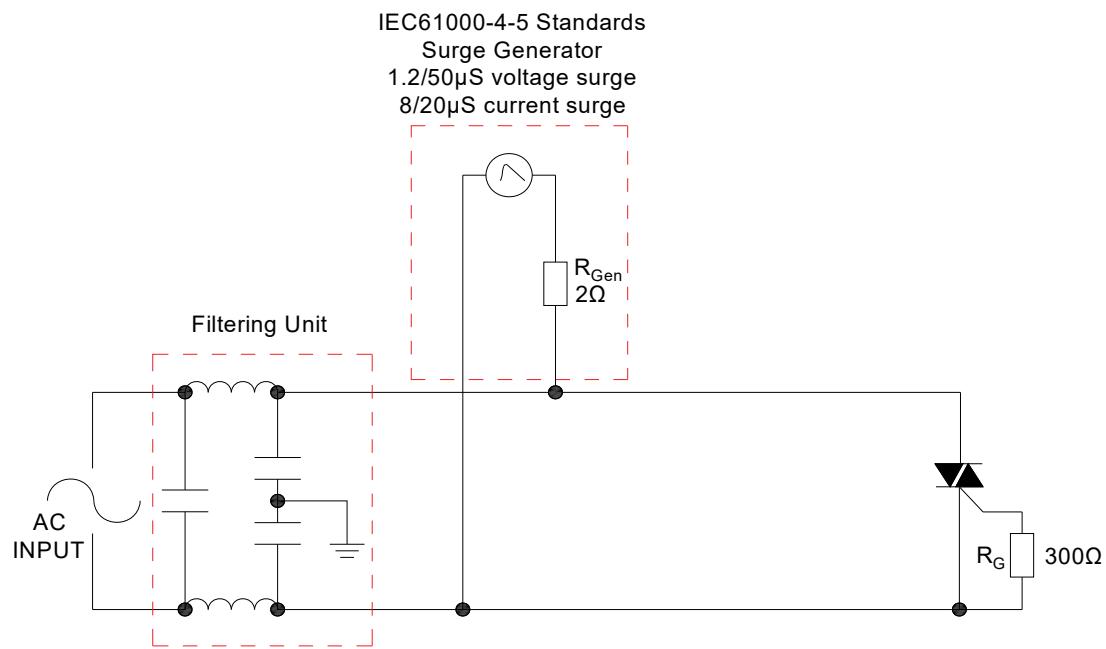


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

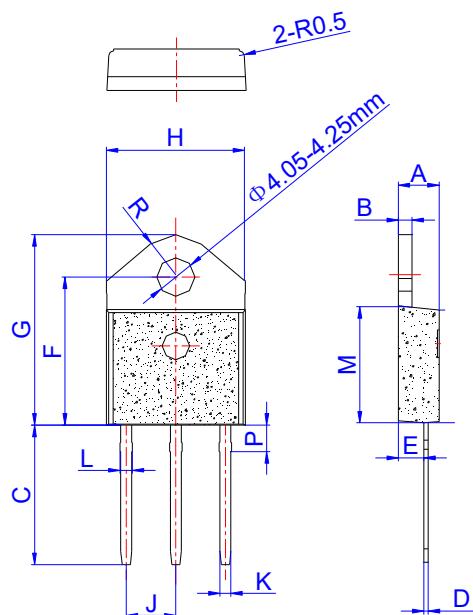
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II -III	IV			
JST41Z-1200B	1200	50	70	TO-3P(Ins)	30	Tube

Document Revision History

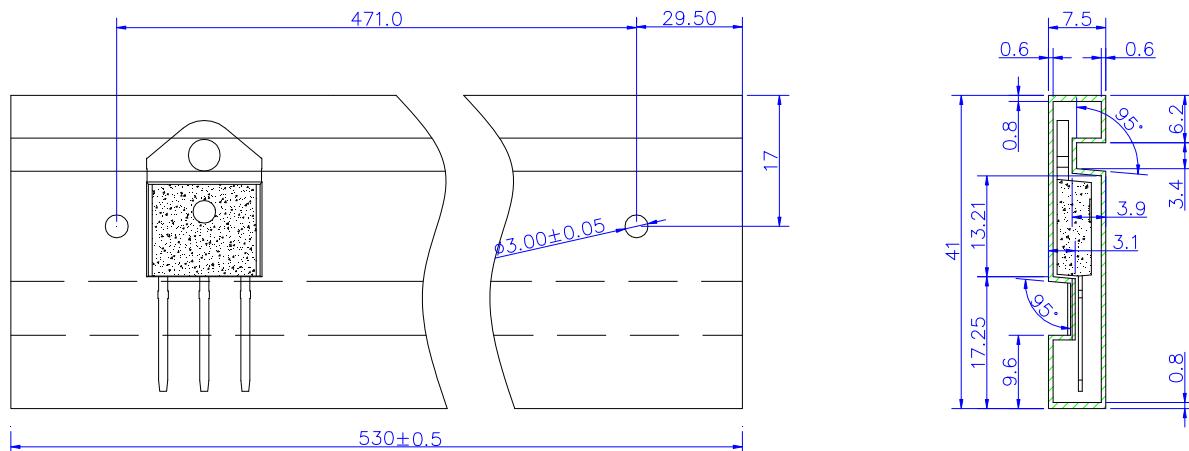
Date	Revision	Changes
May.18, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250

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